

**Supporting Information**

Polythiophene-nanoWO<sub>3</sub> Bilayer as Electrochromic Infrared Filter: An  
Optically Transparent Heat Shield

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**WO<sub>3</sub> synthesis procedure:**

1. 1.25 g of H<sub>2</sub>WO<sub>4</sub> was added to a solution of 30 mL water and 10 mL H<sub>2</sub>O<sub>2</sub> under stirring at 90<sup>0</sup>C.
2. The above solution turned transparent after few minutes then dilute it with water to make 0.05 M.
3. A second aqueous solution (3mL) was prepared by adding 0.035 g of SC(NH<sub>2</sub>)<sub>2</sub> and 0.040 g of C<sub>4</sub>H<sub>4</sub>O<sub>4</sub>.
4. Then add aqueous HCl (3M, 2mL), CH<sub>3</sub>CN (18mL) and the (0.05M, 1mL) H<sub>2</sub>WO<sub>4</sub> solution prepared in step 2 to the above solution.
5. The resultant solution was transferred to a teflon lined auto clave containing FTO glass substrates and heated in an oven at 180<sup>0</sup>C for 3 hours. Allow it to cool at room temperature and substrates were rinsed with water and oven dried for 1 hour at 50<sup>0</sup>C.

**Steps involved in device fabrication:**

1. FTO coated glass substrate has been spin coated with 0.06 wt% of P3HT in DCB at 600 rpm for 120 seconds and annealed at 50<sup>0</sup>C for 1 hour.
2. The above P3HT deposited FTO substrate is sandwiched with WO<sub>3</sub> substrate (fabricated using above recipe) with the help of a patterned double sided tape.
3. LiClO<sub>4</sub> in PEO matrix is used as an electrolyte filled in between two substrates in above fabricated device.

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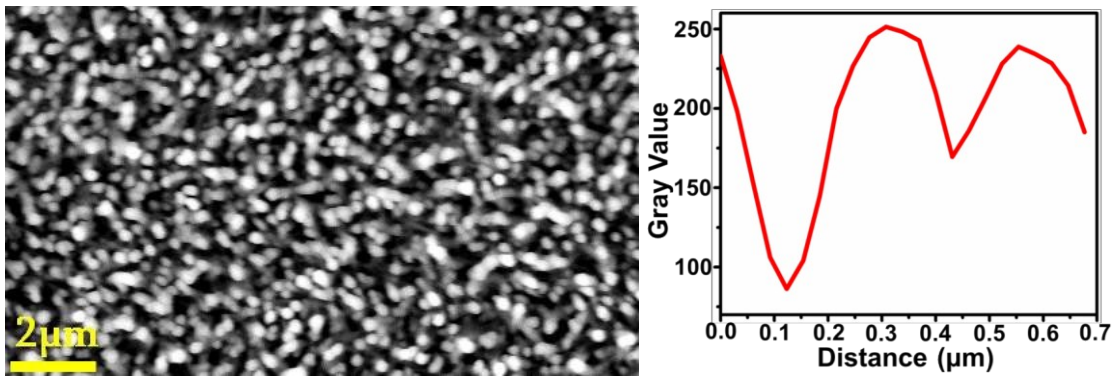


Figure S1: SEM image and corresponding line profile analysis using Image J.

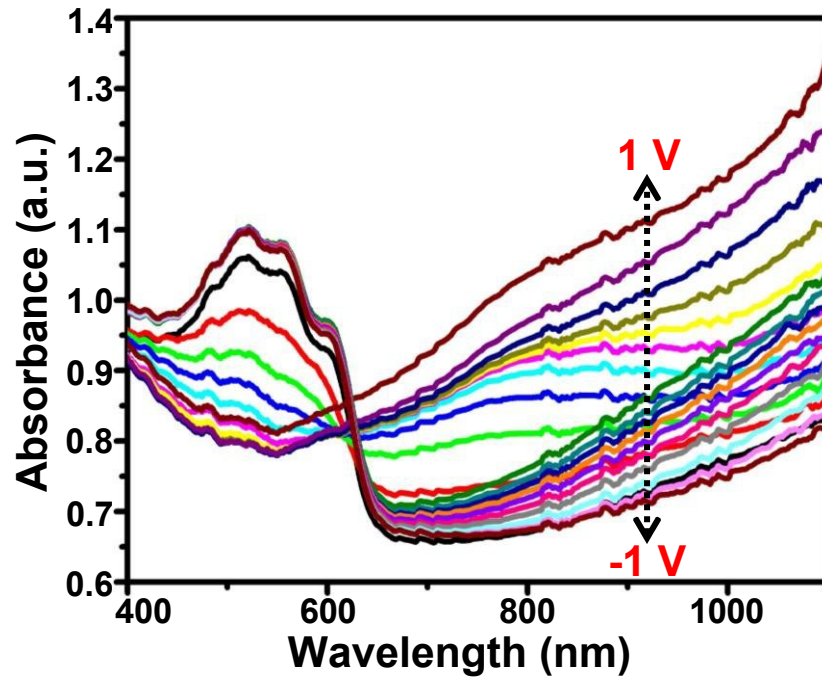


Figure S2: In situ Visible Infrared spectra of device with various applied bias ranging from 1 V to -1V.

Table S1: Comparison of heat shielding parameters of electrochromic device containing tungsten as one of the element.

S. No.	Device composition	Voltage (V)	Switching time (s)	$\Delta A$	Colour of device during absorption of IR	Reference
1.	P3HT/WO <sub>3</sub>	$\pm 1V$	0.05	0.4	Transparent	This work
2.	P <sub>8</sub> W <sub>48</sub> /W <sub>18</sub> O <sub>49</sub>	-1 V & 0.4 V	86	0.8	Blue	Gu et al <sup>[1]</sup>
3.	W <sub>18</sub> O <sub>49</sub>	1.5V & -1V	8	0.3	Blue	Li et al <sup>[2]</sup>
4.	WO <sub>3</sub> /PEDOT:PSS	$\pm 1V$	1.2	0.4	Dark blue	Jian et al <sup>[3]</sup>
5.	WO <sub>3</sub> .2H <sub>2</sub> O	$\pm 3V$	9.7	0.6	Blue	Liang et al <sup>[4]</sup>

Table S2: Comparison e electrochromic performance of various hybrid devices.

S. No.	Device composition	Switching time (s)	Voltage (V)	CE (cm <sup>2</sup> /C)	References
1.	P3HT/WO <sub>3</sub>	0.05	1	378	This work
2.	WO <sub>3</sub> /PANI	0.5	2	312	Eran et al <sup>[5]</sup>
3.	WO <sub>3</sub> /RGO/Ag NW	8	1	53.1	Mallikarjuna et al <sup>[6]</sup>
4.	PEDOT/graphene/Ag NW	4.1	-1	NR	Deng et al <sup>[7]</sup>
5.	Ag NW/WO <sub>3</sub>	1.7	1	80.2	Shen et al <sup>[8]</sup>
6.	Mesoporous WO <sub>3</sub>	2.4	-2	79.7	Wang et al <sup>[9]</sup>
7.	WO <sub>3</sub> /PEDOT	NR	2	NR	Dulgerbaki et al <sup>[10]</sup>
8.	P3HT/WO <sub>3</sub>	1.3	1	NR	Kim et al <sup>[11]</sup>
9.	P3HT/GO	20	2	NR	Kim et al <sup>[12]</sup>
10.	WO <sub>3</sub> /V <sub>2</sub> O <sub>5</sub>	4.4	1.5	87.1	Tang et al <sup>[13]</sup>

## References:

- [1] H. Gu, C. Guo, S. Zhang, L. Bi, T. Li, T. Sun, S. Liu, *ACS Nano* **2018**, *12*, 559.
- [2] G. Li, S. Zhang, C. Guo, S. Liu, *Nanoscale* **2016**, *8*, 9861.
- [3] C.-W. Chang-Jian, E.-C. Cho, S.-C. Yen, B.-C. Ho, K.-C. Lee, J.-H. Huang, Y.-S. Hsiao, *Dyes and Pigments* **2018**, *148*, 465.
- [4] L. Liang, J. Zhang, Y. Zhou, J. Xie, X. Zhang, M. Guan, B. Pan, Y. Xie, *Scientific Reports* **2013**, *3*, 1936.
- [5] E. Eren, C. Alver, G. Yurdabak Karaca, E. Uygun, A. Uygun Oksuz, *Synthetic Metals* **2018**, *235*, 115.
- [6] K. Mallikarjuna, H. Kim, *ACS Appl. Mater. Interfaces* **2019**, *11*, 1969.
- [7] B. Deng, P.-C. Hsu, G. Chen, B. N. Chandrashekar, L. Liao, Z. Ayitimuda, J. Wu, Y. Guo, L. Lin, Y. Zhou, M. Aisijiang, Q. Xie, Y. Cui, Z. Liu, H. Peng, *Nano Lett.* **2015**, *15*, 4206.
- [8] L. Shen, L. Du, S. Tan, Z. Zang, C. Zhao, W. Mai, *Chemical Communications* **2016**, *52*, 6296.
- [9] W. Wang, X. Wang, X. Xia, Z. Yao, Y. Zhong, J. Tu, *Nanoscale* **2018**, *10*, 8162.
- [10] C. Dulgerbaki, A. U. Oksuz, *Electroanalysis* **2014**, *26*, 2501.
- [11] T.-H. Kim, H. J. Jeon, J.-W. Lee, Y.-C. Nah, *Electrochemistry Communications* **2015**, *57*, 65.
- [12] T.-H. Kim, K.-I. Choi, H. Kim, S. H. Oh, J. Koo, Y.-C. Nah, *ACS Appl. Mater. Interfaces* **2017**, *9*, 20223.
- [13] K. Tang, Y. Zhang, Y. Shi, J. Cui, X. Shu, Y. Wang, J. Liu, J. Wang, H. Hoe Tan, Y. Wu, *Journal of Materials Chemistry C* **2018**, *6*, 12206.